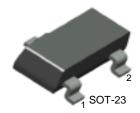


KST6428

Amplifier Transistor



NPN Epitaxial Silicon Transistor

1. Base 2. Emitter 3. Collector

Absolute Maximum Ratings T_a =25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	60	V
√ _{CEO}	Collector-Emitter Voltage	50	V
√ _{EBO}	Emitter-Base Voltage	6	V
С	Collector Current	200	mA
°c	Collector Dissipation	350	mW
Г _{STG}	Storage Temperature	150	°C

Refer to KST5088 for graphs

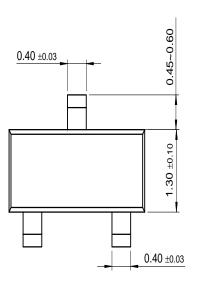
$\textbf{Electrical Characteristics} \ \, \textbf{T}_{a} \!\!=\!\! 25^{\circ} \textbf{C} \ \, \text{unless otherwise noted}$

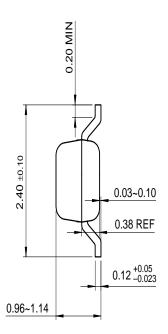
Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =100μA, I _E =0	60		V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =1mA, I _B =0	50		V
I _{CBO}	Collector Cut-off Current	V_{CB} =30V, I_{E} =0		0.01	μΑ
I _{CEO}	Collector Cut-off Current	$V_{CE}=30V$, $I_{B}=0V$		0.1	μΑ
I _{EBO}	Emitter Cut-off Current	V _{EB} =5V, I _C =0		0.01	μΑ
h _{FE}	DC Current Gain	$\begin{tabular}{llll} V_{CE}=5V, I_{C}=0.01mA \\ V_{CE}=5V, I_{C}=0.1mA \\ V_{CE}=5V, I_{C}=1.0mA \\ V_{CE}=5V, I_{C}=10mA \\ \end{tabular}$	250 250 250 250	650	V
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =10mA, I _B =0.5mA I _C =100mA, I _B =5mA		0.2 0.6	V V
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} =5V, I _C =1mA	0.56	0.66	pF
C _{ob}	Output Capacitance	V _{CB} =10V, I _E =0, f=1MHz		3	MHz
f _T	Current Gain Bandwidth Product	V _{CE} =5V, I _C =0mA, f=100MHz	100	700	

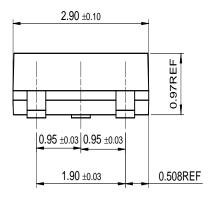


Package Demensions

SOT-23







Dimensions in Millimeters

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